

ABSTRACT

A nitride semiconductor light-emitting device includes a layered portion emitting light on a substrate. The layered
5 portion includes an n-type semiconductor layer, an active layer, and a p-type semiconductor layer. The periphery of the layered portion is inclined, and the surface of the n-type semiconductor layer is exposed at the periphery. An n electrode is disposed on the exposed surface of the n-type semiconductor layer. This
10 device structure can enhance the emission efficiency and the light extraction efficiency.